

# 2SC5658M3T5G, 2SC5658RM3T5G

## NPN Silicon General Purpose Amplifier Transistor

This NPN transistor is designed for general purpose amplifier applications. This device is housed in the SOT-723 package which is designed for low power surface mount applications, where board space is at a premium.

### Features

- Reduces Board Space
- High  $h_{FE}$ , 210–460 (typical)
- Low  $V_{CE(sat)}$ , < 0.5 V
- ESD Performance: Human Body Model; > 2000 V, Machine Model; > 200 V
- Available in 8 mm, 7-inch/3000 Unit Tape and Reel
- These are Pb-Free Devices

### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

Rating	Symbol	Value	Unit
Collector-Base Voltage	$V_{(BR)CBO}$	50	Vdc
Collector-Emitter Voltage	$V_{(BR)CEO}$	50	Vdc
Emitter-Base Voltage	$V_{(BR)EBO}$	5.0	Vdc
Collector Current – Continuous	$I_C$	100	mAdc

### THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation (Note 1)	$P_D$	260	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 ~ +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

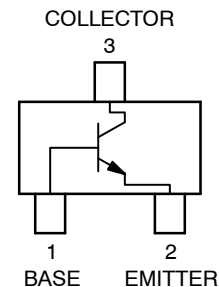
1. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.



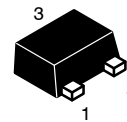
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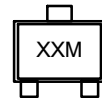
## NPN GENERAL PURPOSE AMPLIFIER TRANSISTORS SURFACE MOUNT



### MARKING DIAGRAM



SOT-723  
CASE 631AA



XX = Specific Device Code  
(B9 = 2SC5658M3T5G  
RM = 2SC5658RM3T5G)  
M = Date Code

### ORDERING INFORMATION

Device	Package	Shipping†
2SC5658M3T5G	SOT-723 (Pb-Free)	3000/Tape & Reel
2SC5658RM3T5G	SOT-723 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C)

Characteristic	Symbol	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage (I <sub>C</sub> = 50 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	50	–	–	Vdc
Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	50	–	–	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 50 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)EBO</sub>	5.0	–	–	Vdc
Collector-Base Cutoff Current (V <sub>CB</sub> = 30 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	–	–	0.5	μA
Emitter-Base Cutoff Current (V <sub>EB</sub> = 4.0 Vdc, I <sub>B</sub> = 0)	I <sub>EBO</sub>	–	–	0.5	μA
Collector-Emitter Saturation Voltage (Note 2) (I <sub>C</sub> = 60 mAdc, I <sub>B</sub> = 5.0 mAdc)	V <sub>CE(sat)</sub>	–	–	0.4	Vdc
DC Current Gain (Note 2) (V <sub>CE</sub> = 6.0 Vdc, I <sub>C</sub> = 1.0 mAdc)      2SC5658M3T5G (V <sub>CE</sub> = 6.0 Vdc, I <sub>C</sub> = 1.0 mAdc)      2SC5658RM3T5G	h <sub>FE</sub>	120 215	– –	560 375	–
Transition Frequency (V <sub>CE</sub> = 12 Vdc, I <sub>C</sub> = 2.0 mAdc, f = 30 MHz)	f <sub>T</sub>	–	180	–	MHz
Output Capacitance (V <sub>CB</sub> = 12 Vdc, I <sub>C</sub> = 0 Adc, f = 1.0 MHz)	C <sub>OB</sub>	–	2.0	–	pF

2. Pulse Test: Pulse Width ≤ 300 μs, D.C. ≤ 2%.

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## TYPICAL ELECTRICAL CHARACTERISTICS

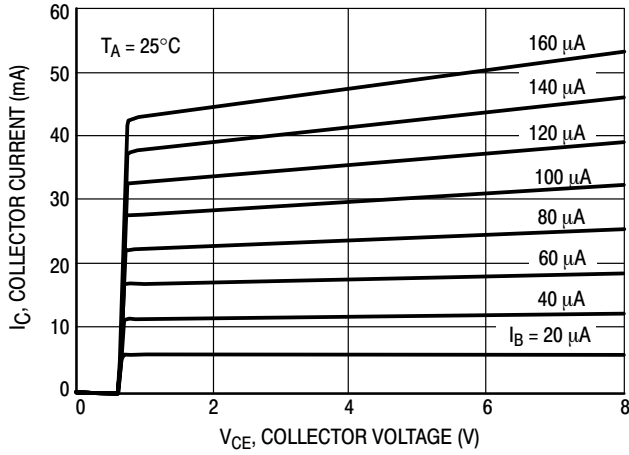


Figure 1.  $I_C - V_{CE}$

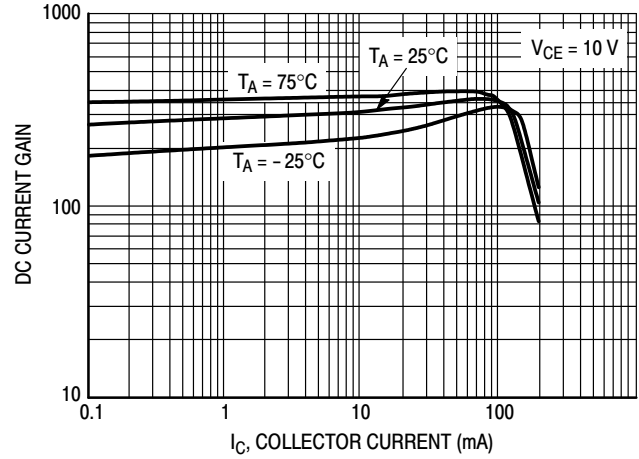


Figure 2. DC Current Gain

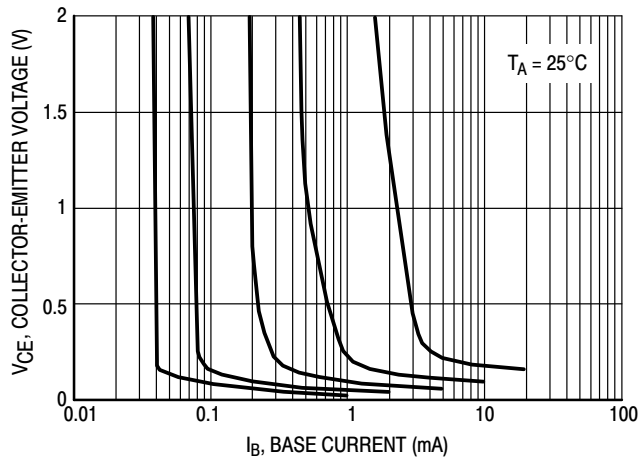


Figure 3. Collector Saturation Region

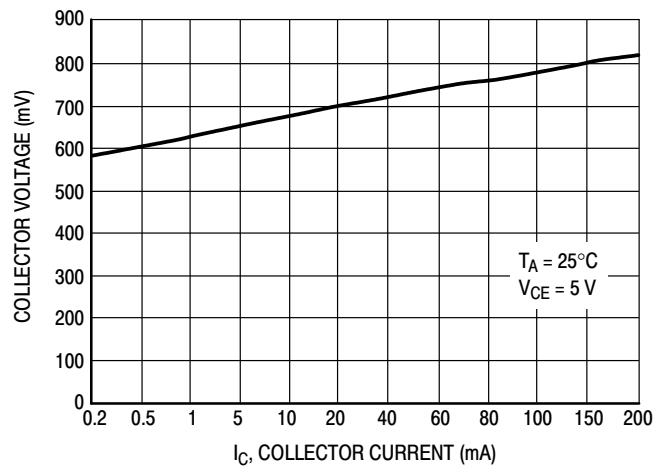


Figure 4. On Voltage

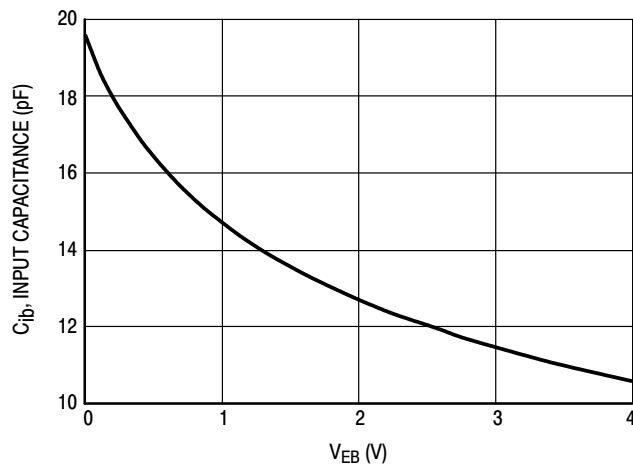


Figure 5. Capacitance

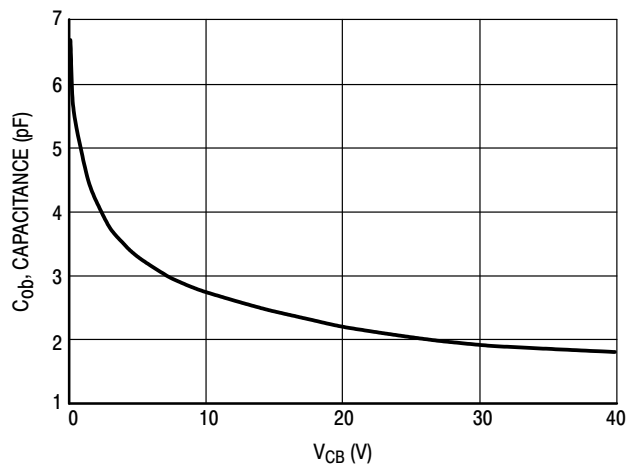
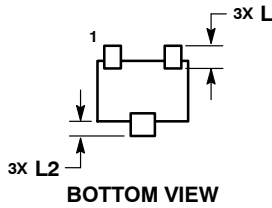
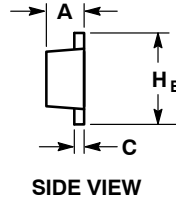
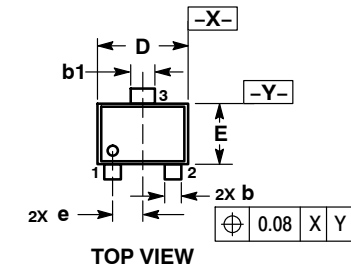


Figure 6. Capacitance

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## PACKAGE DIMENSIONS

SOT-723  
CASE 631AA-01  
ISSUE D

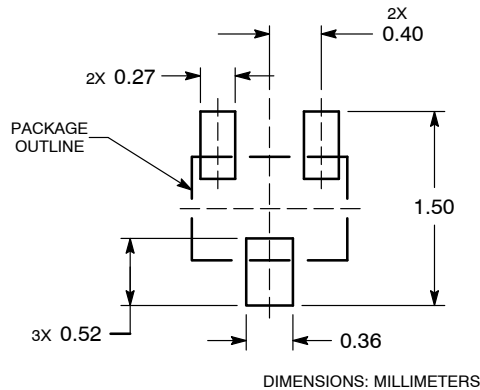


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
C	0.07	0.12	0.17
D	1.15	1.20	1.25
E	0.75	0.80	0.85
e	0.40 BSC		
H E	1.15	1.20	1.25
L	0.29 REF		
L2	0.15	0.20	0.25

### RECOMMENDED SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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